



MT20N024

主要参数 MAIN CHARACTERISTICS

I_D	80A
V_{DS}	200V
$R_{dson-max}$ (@ $V_{GS}=10V$)	24m Ω
Q_g-typ	98nC

用途

- 电信与工业领域隔离 DC/DC 转换
- 同步整流领域
- 汽车应用
- 不间断电源

APPLICATIONS

- Isolated DC/DC Converters in Telecom and Industrial
- Synchronous Rectification
- Automotive
- UPS

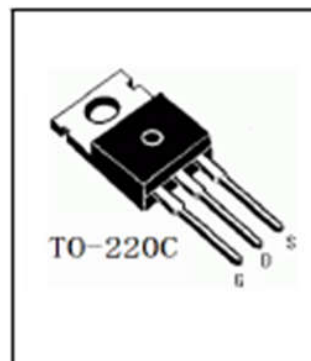
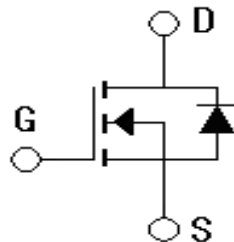
产品特性

- 低栅极电荷
- 低 R_{dson}
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Low R_{dson}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
MT20N024-C-B	MT20N024-C-BR	N/A	N/A	MT20N024	TO-220C



绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
		MT20N024	
最高漏极-源极直流电压 Drain-Source Voltage	V_{DSS}	200	V
连续漏极电流 Drain Current -continuous	I_{D} $T=25^{\circ}\text{C}$	80*	A
	I_{D} $T=100^{\circ}\text{C}$	64*	A
最大脉冲漏极电流 (注1) Drain Current - pulse (note 1)	I_{DM}	320*	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	+30/-30V	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	145	mJ
雪崩电流 (注1) Avalanche Current (note 1)	I_{AS}	54	A
耗散功率 Power Dissipation	P_{D} $T_c=25^{\circ}\text{C}$ -Derate above 25°C	420	W
		3.36	W/ $^{\circ}\text{C}$
最高结温及存储温度 Operating and Storage Temperature Range	$T_{\text{J}}, T_{\text{STG}}$	-55~+150	$^{\circ}\text{C}$
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_{L}	300	$^{\circ}\text{C}$

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	200	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V, V_{GS}=0V,$ $T_C=25^{\circ}C$	-	-	10	μA
		$V_{DS}=160V, V_{GS}=0V,$ $T_C=100^{\circ}C$	-	-	200	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	3	4	5	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=46A$	-	20	24	m Ω
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	6212	-	pF
输出电容 Output capacitance	C_{oss}		-	471	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	60	-	pF
栅电阻 Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V,$ $F=1MHz$	-	0.7	-	Ω



**电特性 ELECTRICAL CHARACTERISTICS****开关特性 Switching Characteristics**

延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=100V, I_D=46A, R_G=25\Omega$ $V_{GS}=10V$ (note 3, 4)	-	28	-	ns
上升时间 Turn-On rise time	t_r		-	89	-	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	39	-	ns
下降时间 Turn-Off Fall time	t_f		-	68	-	ns
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=100V$, $I_D=46A$ $V_{GS}=10V$ (note 3, 4)	-	98	-	nC
栅-源电荷 Gate-Source charge	Q_{gs}		-	42	-	nC
栅-漏电荷 Gate-Drain charge	Q_{gd}		-	22	-	nC

漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings

正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$T_J=25^\circ C, V_{GS}=0V, I_S=46A$	-	-	0.9	V
正向连续电流 Diode continuous forward current	I_S	$V_G=V_D=0V$, force current			80	A
正向脉冲电流 Diode pulse current	I_{SM}				320	A
反向恢复时间 Reverse recovery time	T_{rr}	$T_J=25^\circ C, V_{GS}=0V, I_F=46A$,	-	86	-	ns
反向恢复电荷 Reverse recovery charge	Q_{rr}	$V_{DD}=50V, dI_F/dt=100A/\mu A$ (note 3)	-	338	-	nC

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max	单位 Unit
		MT20N024	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.297	$^\circ C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	45.78	$^\circ C/W$

注释:

1: 脉冲宽度由最高结温限制

2: $V_{DD}=25V, L=0.1mH, R_G=25\Omega, I_{AS}=54A$ 起始结温
 $T_J=25^\circ C$ 3: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$

4: 基本与工作温度无关

Notes:

1: Pulse width limited by maximum junction
temperature2: $V_{DD}=25V, L=0.1mH, R_G=25\Omega, I_{AS}=54A$ Starting
 $T_J=25^\circ C$ 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

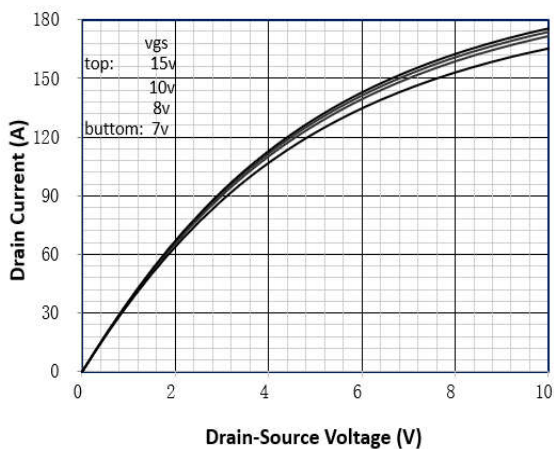
4: Essentially independent of operating temperature



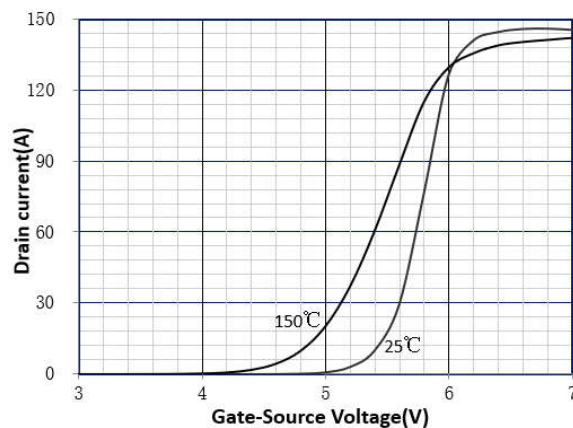


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

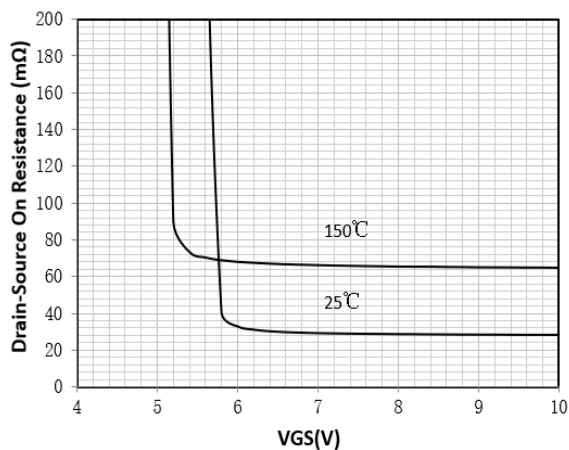
On-Region Characteristics



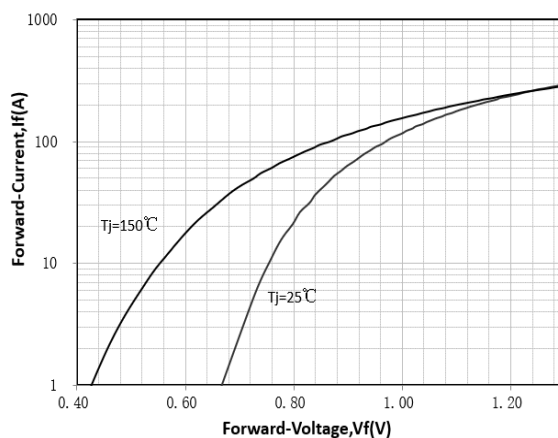
Transfer Characteristics



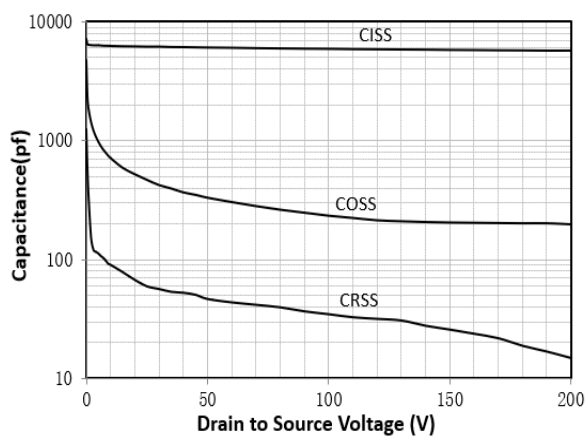
On-Resistance Variation vs. Drain Current and Gate Voltage



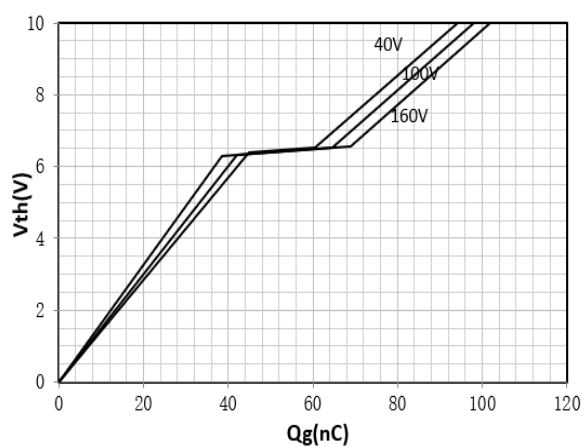
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics

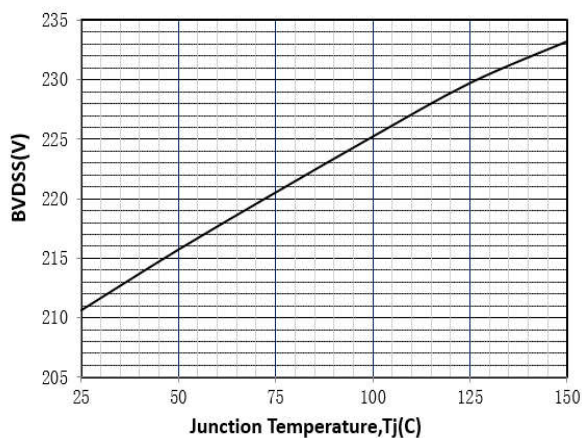
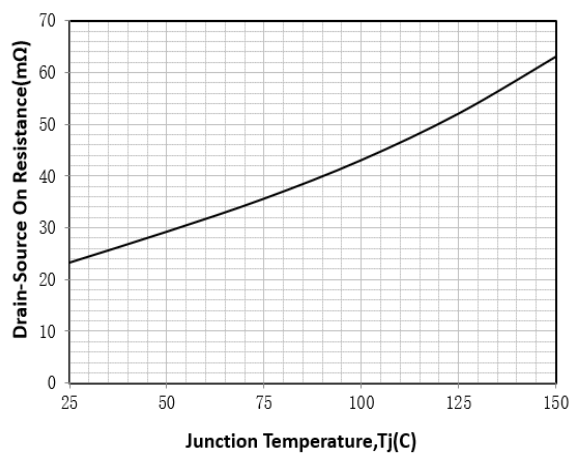
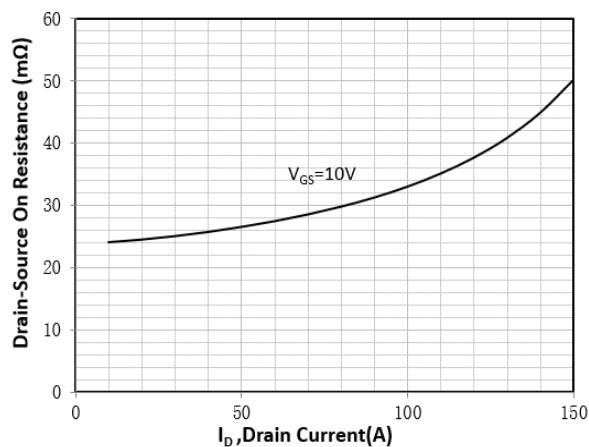
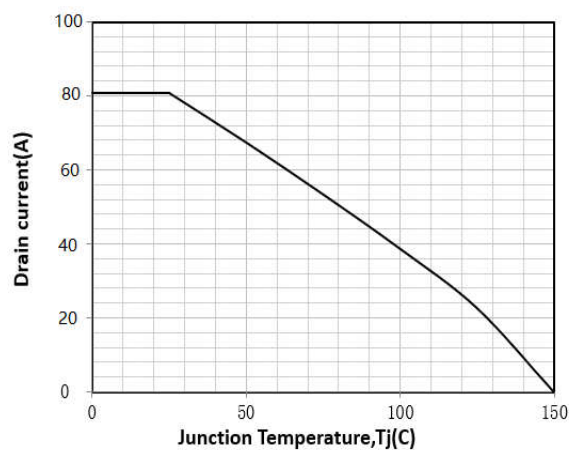


Gate Charge Characteristics

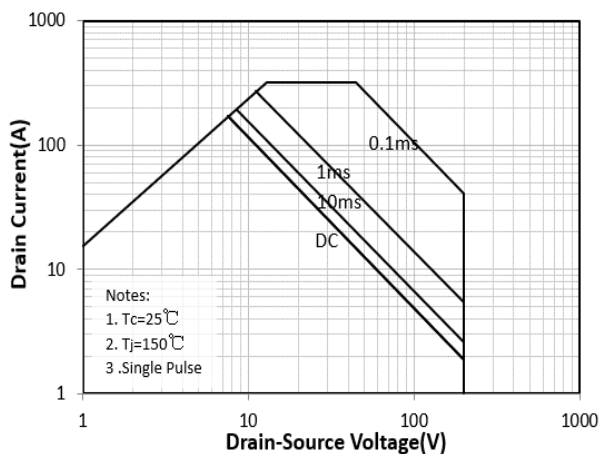




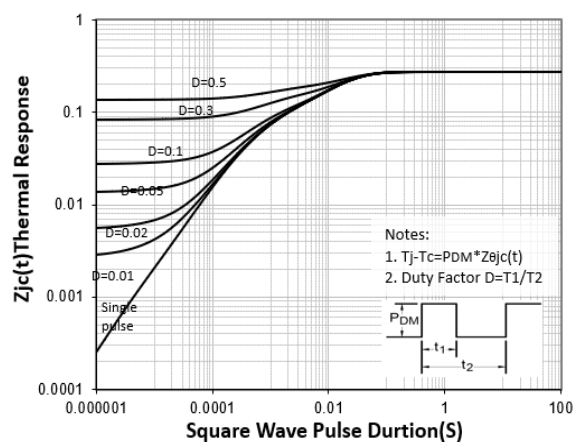
特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation
vs. TemperatureOn-Resistance Variation
vs. TemperatureOn-Resistance vs. Drain Current
and Gate VoltageMaximum Drain Current
vs. Case Temperature

Maximum Safe Operation Area



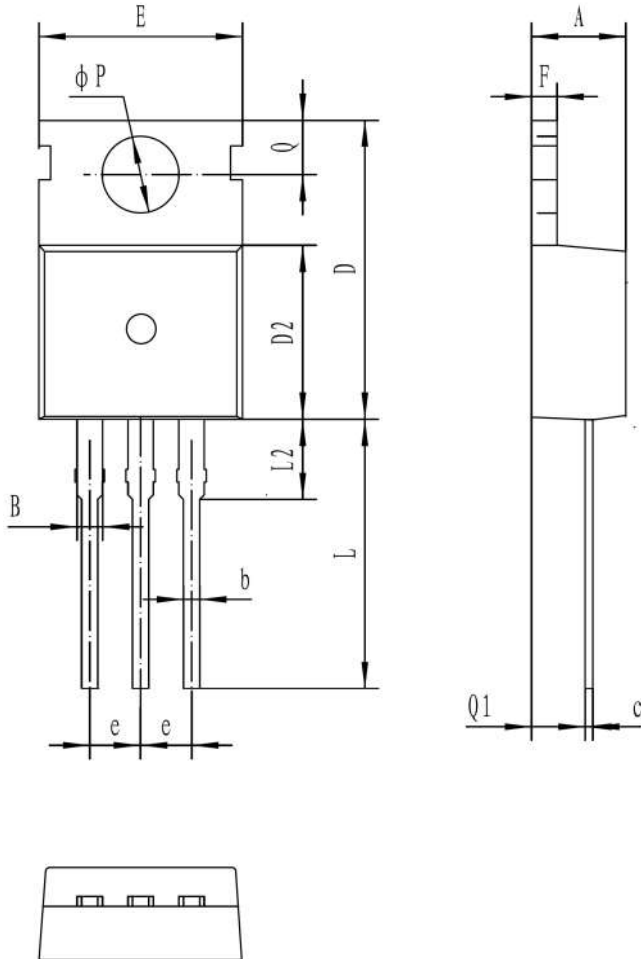
On-Region Characteristics





TO-220C

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



**注意事项**

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